	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

			±		

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

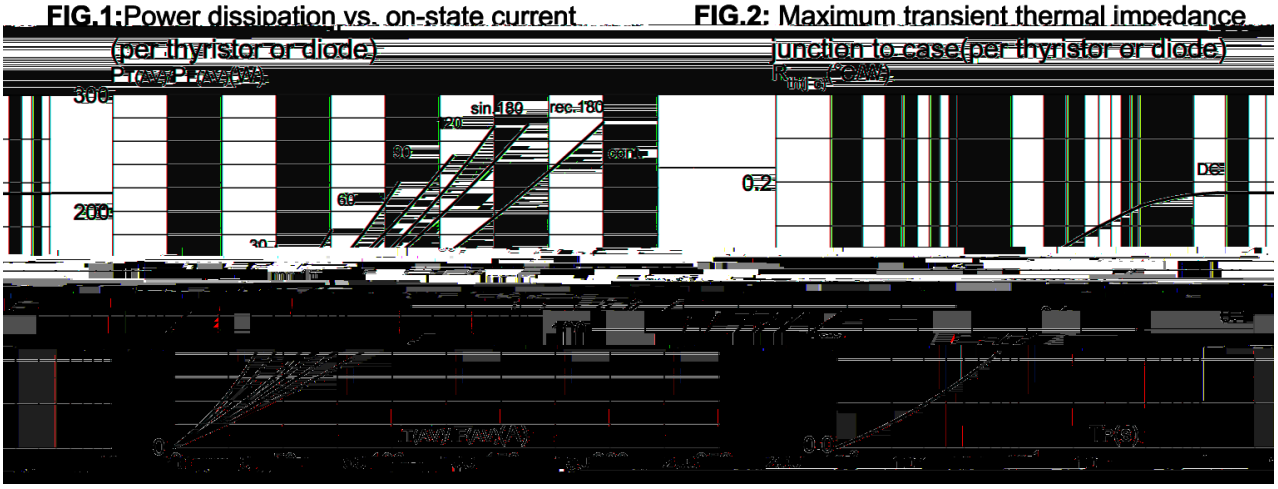

FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

FIG.5 Gate trigger characteristics

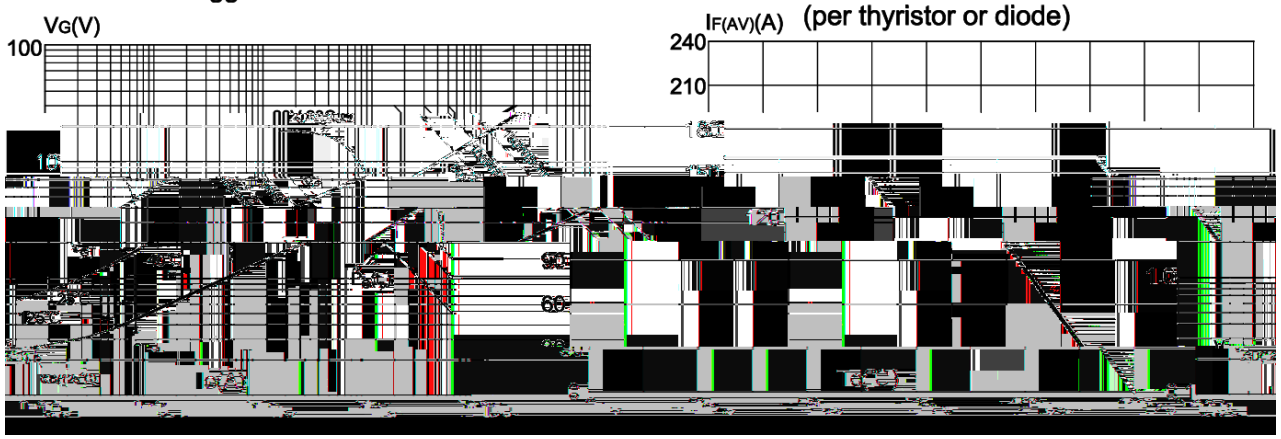

FIG.6: Forward current vs. case temperature (per thyristor or diode)